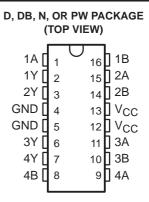
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- Inputs Are TTL-Voltage Compatible
- Center-Pin V<sub>CC</sub> and GND Configurations to Minimize High-Speed Switching Noise
- EPIC<sup>™</sup> (Enhanced-Performance Implanted CMOS) 1-µm Process
- 500-mA Typical Latch-Up Immunity at 125°C
- Package Options Include Plastic Small-Outline Packages (D), Plastic Shrink Small-Outline Packages (DB), Plastic Thin Shrink Small-Outline Packages (PW), and Standard Plastic 300-mil DIPs (N)



#### description

This device contains four independent 2-input OR gates. It performs the Boolean function Y = A + B or  $Y = \overline{A} \bullet \overline{B}$  in positive logic.

The 74ACT11032 is characterized for operation from -40°C to 85°C

# FUNCTION TABLE (each gate)

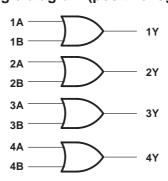
			737 17
	INP	JTS	OUTPUT
	A	В	Y
-	H	X	H
	X	Н	Н
	L	L	L

#### logic symbol†

4		
1A 16	2	2 1Y
1B		11
15 2A		
14		3 2Y
2B 11		
3A		6
		3Y
3B <u>9</u>		
4A		7
3B		4Y
		l

<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

#### logic diagram (positive logic)





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## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>	0.5 V to 6V
Input voltage range, V <sub>I</sub> (see Note 1)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Output voltage range, VO (see Note 1)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, $I_{IK}$ ( $V_I < 0$ or $V_I > V_{CC}$ )	±20 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> )	±50 mA
Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$	±50 mA
Continuous current through V <sub>CC</sub> or GND	±100 mA
Maximum power dissipation at $T_A = 55^{\circ}$ C (in still air) (see Note 2	): D package 1.3 W
	DB package 0.55 W
	N package1.1 W
	PW package 0.5 W
Storage temperature range, T <sub>stq</sub>	– 65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
  - 2. The maximum package power dissipation is calculated using a junction temperature of 150 °C and a board trace length of 750 mils, except for the N package, which has a trace length of zero.

#### recommended operating conditions

	20 73	MIN	MAX	UNIT
VCC	Supply voltage	4.5	5.5	٧
VIH	High-level input voltage	2		V
V <sub>IL</sub>	Low-level input voltage		0.8	V
VI	Input voltage	0	VCC	V
Vo	Output voltage	0	VCC	V
loh	High-level output current		-24	mA
loL	Low-level output current		24	mA
Δt/Δν	Input transition rise or fall rate	0	10	ns/V
TA	Operating free-air temperature	-40	85	°C



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# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	vcc	T <sub>A</sub> = 25°C			MIN	MAX	UNIT
PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	IVIIIN	WAX	UNII
	I <sub>OH</sub> = -50 μA	4.5 V	4.4			4.4		
		5.5 V	5.4			5.4		V
Voн	04.04	4.5 V	3.94			3.8		
	I <sub>OH</sub> = -24 mA		4.94			4.8		
	$I_{OH} = -75 \text{ mA}^{\dagger}$	5.5 V				3.85		
	I <sub>OL</sub> = 50 μA	4.5 V			0.1		0.1	
		5.5 V			0.1		0.1	V
VOL	I <sub>OL</sub> = 24 mA	4.5 V			0.36		0.44	
		5.5 V			0.36		0.44	
	$I_{OL} = 75 \text{ mA}^{\dagger}$	5.5 V					1.65	
ΙĮ	$V_I = V_{CC}$ or GND	5.5 V			±0.1		±1	μΑ
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V	-		4		40	μΑ
Δl <sub>CC</sub> ‡	One input at 3.4 V, Other inputs at GND or V <sub>CC</sub>	5.5 V	其形		0.9		1	mA
Ci	$V_I = V_{CC}$ or GND	5 V		3.5	·		·	pF

<sup>†</sup> Not more than one output should be tested at a time, and the duration of the test should not exceed 10 ms.

# switching characteristics over recommended ranges of supply voltage and free-air temperature (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	TO (OUTPUT)	T <sub>A</sub> = 25°C			MIN MA	MAX	UNIT
PARAMETER	(INPUT)		MIN	TYP	MAX	IVIIIN	IVIAA	UNIT
t <sub>PLH</sub>	A or B		1.5	6.2	8.1	1.5	9	nc
t <sub>PHL</sub>	AUIB	<b>'</b>	1.5	4.9	7.4	1.5	8	ns

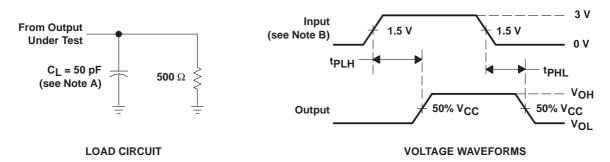
# operating characteristics, $V_{CC} = 5 \text{ V}$ , $T_A = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS		TYP	UNIT
C <sub>pd</sub>	Power dissipation capacitance per gate	$C_L = 50 \text{ pF},$	f = 1 MHz	29	pF

<sup>‡</sup>This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V<sub>CC</sub>.

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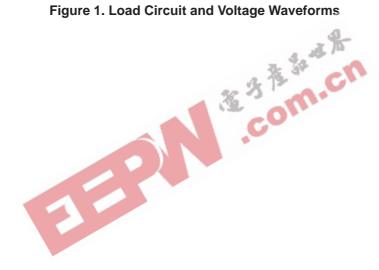
#### PARAMETER MEASUREMENT INFORMATION



NOTES: A.  $C_L$  includes probe and jig capacitance.

- B. Input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub> = 3 ns,  $t_f = 3 \text{ ns.}$
- C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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